



DMV1500L

DAMPER + MODULATION DIODE FOR VIDEO

Table 1: Main Product Characteristics

	DAMPER	MODUL.
I _{F(AV)}	4 A	3 A
V _{RRM}	1500 V	600 V
t _{rr} (max)	170 ns	50 ns
V _F (max)	1.5V	1.4 V

FEATURES AND BENEFITS

- Full kit in one package
- High breakdown voltage capability
- Very fast recovery diode
- Specified turn on switching characteristics
- Low static and peak forward voltage drop for low dissipation
- Insulated version:
Insulated voltage = 2000 V_{RMS}
Capacitance = 7 pF
- Planar technology allowing high quality and best electrical characteristics
- Outstanding performance of well proven DTV as damper and new faster Turbo 2 600V technology as modulation

DESCRIPTION

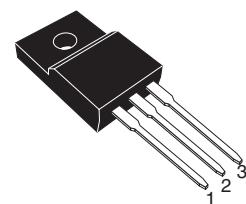
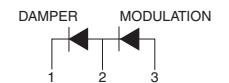
High voltage semiconductor especially designed for horizontal deflection stage in standard and high resolution video display with E/W correction.

The insulated TO-220FPAB package includes both the DAMPER diode and the MODULATION diode, thanks to a dedicated design.

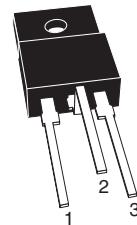
Assembled on automated line, it offers very low dispersion values on insulating and thermal performances.

Table 2: Order Codes

Part Number	Marking
DMV1500LFD	DMV1500L
DMV1500LFD5	DMV1500L



**TO-220FPAB
DMV1500LFD**



**TO-220FPAB F5 Bending
DMV1500LFD5
(optional)**

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Table 3: Absolute Maximum Ratings

Symbol	Parameter	Value		Unit
		Damper	Modul.	
V _{RRM}	Repetitive peak reverse voltage	1500	600	V
I _{FSM}	Surge non repetitive forward current tp = 10ms sinusoidal	50	35	A
T _{stg}	Storage temperature range	-40 to +150		°C
T _j	Maximum operating junction temperature	150		°C

Table 4: Thermal Resistance

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case thermal resistance	4.0	°C/W

Table 5: Static Electrical Characteristics

Symbol	Parameter	Test conditions		Value				Unit
				T _j = 25°C	T _j = 125°C	Typ.	Max.	
		Damper	V _R = 1500 V		100	100	1000	
I _R *	Reverse leakage current	Modul.	V _R = 600 V		20	3	50	µA
		Damper	I _F = 4 A	1.2	1.7	1.1	1.5	
V _F **	Forward voltage drop	Modul.	I _F = 3 A		1.8	1.1	1.4	V

Pulse test: * tp = 5 ms, δ < 2%

** tp = 380 µs, δ < 2%

To evaluate the maximum conduction losses of the **DAMPER** and **MODULATION** diodes use the following equations :

$$\text{DAMPER: } P = 1.2 \times I_F(\text{AV}) + 0.075 \times I_F^2(\text{RMS})$$

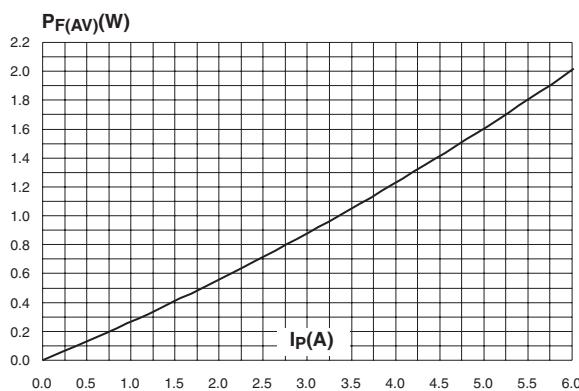
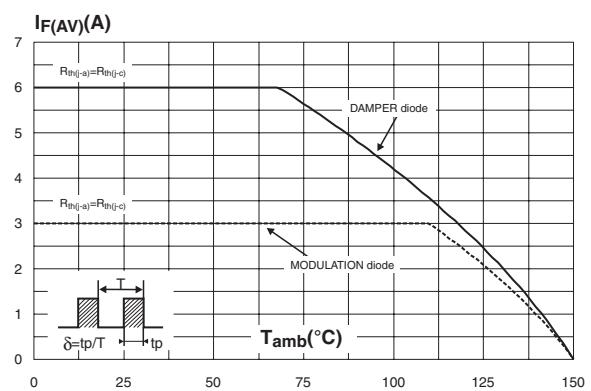
$$\text{MODULATION: } P = 1.12 \times I_F(\text{AV}) + 0.092 \times I_F^2(\text{RMS})$$

Table 6: Recovery Characteristics

Symbol	Parameter	Test conditions		Value				Unit
				Damper	Modul.	Typ.	Max.	
		I _F = 100mA	T _j = 25°C	850		110	350	
t _{rr}	Reverse recovery time	I _R = 100mA						ns
		I _{RR} = 10mA						
		I _F = 1A		130	170	35	50	
		dI _F /dt = -50 A/µs	T _j = 25°C					
		V _R = 30V						

Table 7: Turn-On Switching Characteristics

Symbol	Parameter	Test conditions			Value		Unit
			Typ.	Max.			
t_{fr}	Forward recovery time	Damper	$I_F = 4 \text{ A}$ $dI_F/dt = 80 \text{ A}/\mu\text{s}$ $V_{FR} = 3 \text{ V}$	$T_j = 100^\circ\text{C}$		450	ns
			$I_F = 6.5 \text{ A}$ $dI_F/dt = 50 \text{ A}/\mu\text{s}$ $V_{FR} = 3 \text{ V}$	$T_j = 25^\circ\text{C}$		450	
		Modul.	$I_F = 3 \text{ A}$ $dI_F/dt = 80 \text{ A}/\mu\text{s}$ $V_{FR} = 2 \text{ V}$	$T_j = 100^\circ\text{C}$		240	
V_{FP}	Peak forward voltage	Damper	$I_F = 4 \text{ A}$ $dI_F/dt = 80 \text{ A}/\mu\text{s}$	$T_j = 100^\circ\text{C}$	28	36	V
			$I_F = 6.5 \text{ A}$ $dI_F/dt = 50 \text{ A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	13	17	
		Modul.	$I_F = 3 \text{ A}$ $dI_F/dt = 80 \text{ A}/\mu\text{s}$	$T_j = 100^\circ\text{C}$		8	

Figure 1: Power dissipation versus peak forward current (triangular waveform, $\delta=0.45$)**Figure 2: Average forward current versus ambient temperature**

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Figure 3: Forward voltage drop versus forward current (damper diode)

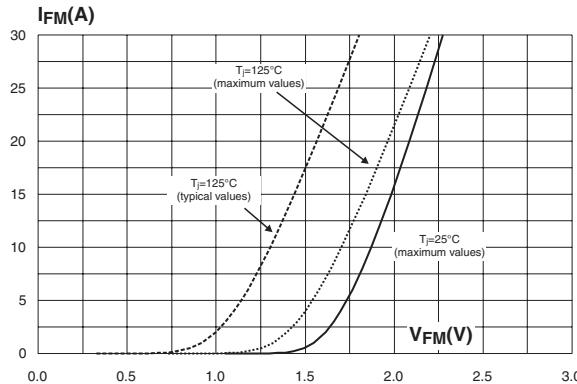


Figure 5: Relative variation of thermal impedance junction to case versus pulse duration

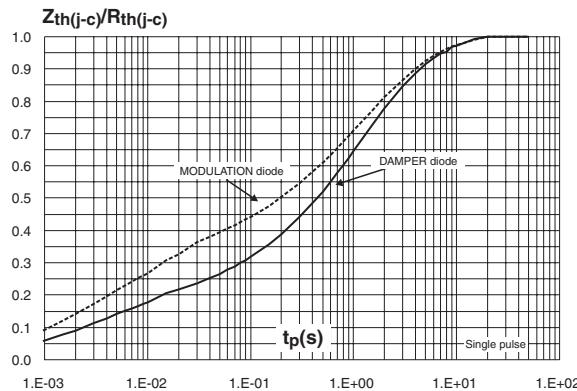


Figure 7: Non repetitive peak forward current versus overload duration (modulation diode)

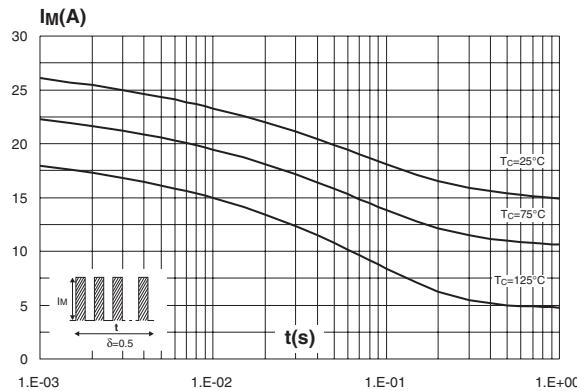


Figure 4: Forward voltage drop versus forward current (modulation diode)

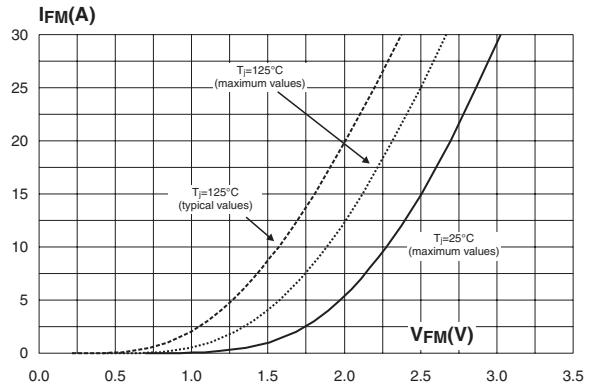


Figure 6: Non repetitive peak forward current versus overload duration (damper diode)

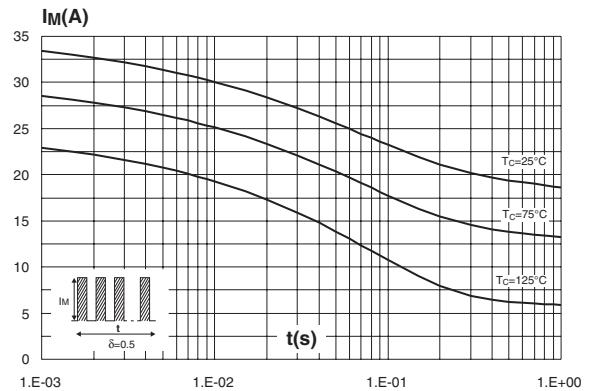


Figure 8: Reverse recovery charges versus dI_F/dt (damper diode)

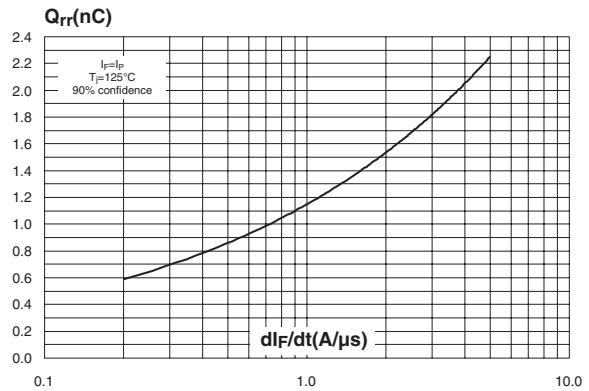


Figure 9: Reverse recovery charges versus dI_F/dt (modulation diode)

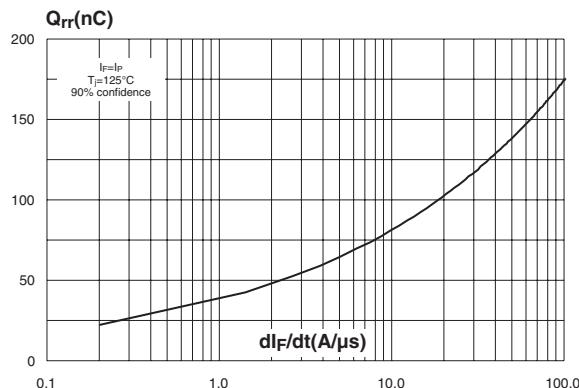


Figure 11: Peak reverse recovery current versus dI_F/dt (modulation diode)

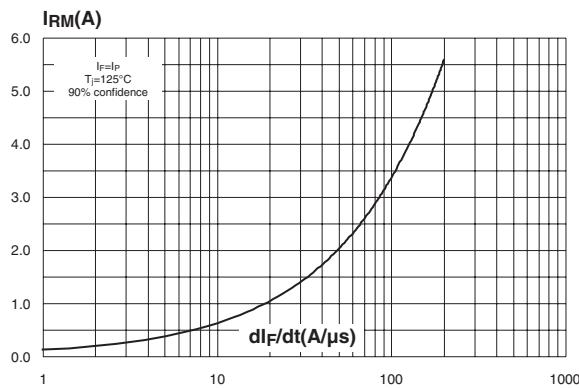


Figure 13: Transient peak forward voltage versus dI_F/dt (modulation diode)

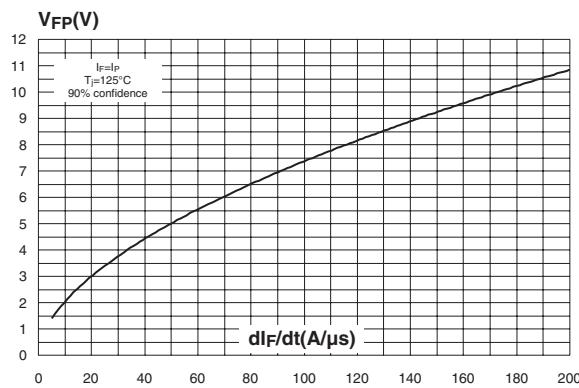


Figure 10: Peak reverse recovery current versus dI_F/dt (damper diode)

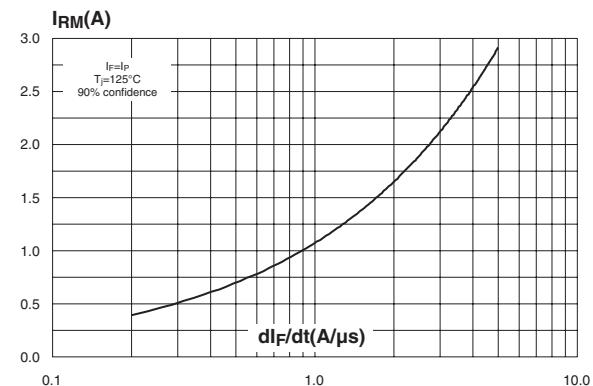


Figure 12: Transient peak forward voltage versus dI_F/dt (damper diode)

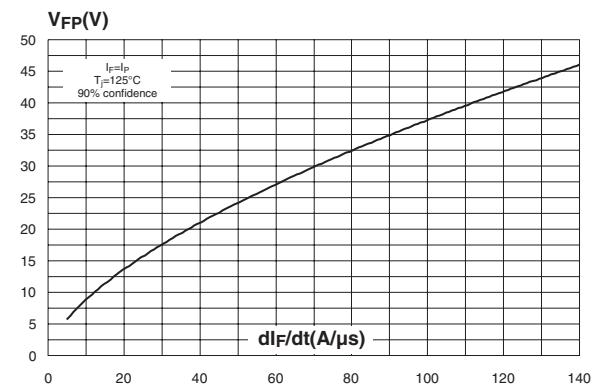


Figure 14: Forward recovery time versus dI_F/dt (damper diode)

